

IN THE CLAIMS:

1. (Currently Amended) A hybrid substrate comprising:
a substrate having a plurality of pockets patterned thereon; and
at least two different materials ~~arrangements~~ deposited within a respective pocket of the plurality of pockets.
2. (Currently Amended) The hybrid substrate according to Claim 1, wherein the at least two different materials ~~arrangements~~ are approximately co-planar with a top surface of the substrate.
3. (Currently Amended) The hybrid substrate according to Claim 1, wherein the at least two different materials ~~arrangements~~ are bonded to the substrate.
4. (Currently Amended) The hybrid substrate according to Claim 1, wherein each of the at least two different materials ~~arrangements~~ is selected from the group consisting of GaAs, InP, silicon wafer, GaN-based high-electron-mobility transistors (HEMTs), and optoelectronic devices.
5. (Original) The hybrid substrate according to Claim 1, wherein the substrate is selected from the group consisting of AlN, quartz, glass, ceramic, CVD diamond, and sapphire.
6. (Original) The hybrid substrate according to Claim 1, wherein the substrate is a high thermal conductive substrate.
7. (Currently Cancelled)
- 8-18. (Previously Withdrawn)